

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Rule 1.53(b) Divisional Application of Serial No. 09/102,665:

Hideki MATSUMURA et al.

Serial No.: Not yet assigned

Group Art Unit: **1763** (Expected)

Filed: **January 10, 2002**

Examiner: **Lund, J.** (Expected)

For: **METHOD AND APPARATUS FOR DEPOSITING A THIN FILM,
AND SEMICONDUCTOR DEVICE HAVING A SEMICONDUCTOR-
INSULATOR JUNCTION**

INFORMATION DISCLOSURE STATEMENT
PURSUANT TO 37 CFR 1.97(b)

Commissioner for Patents
Washington, D.C. 20231

January 10, 2002

Sir:

This Information Disclosure Statement is being filed in order to comply with Applicants' duty of disclosure under 37 CFR 1.56. The documents listed on the Form PTO-1449 were made of record in parent Serial No. 09/102,665 filed on June 23, 1998, and grandparent application Serial No. 08/924,304 filed on September 5, 1997.

The Commissioner is authorized to charge our Deposit Account No. 01-2340 for any fee which is deemed by the Patent and Trademark Office to be required to effect consideration of this statement.

Respectfully submitted,

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Enclosure: PTO-1449



**INFORMATION
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Atty. Docket No. **971003B**

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Applicants: **Hideki MATSUMURA et al.**

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U.S. PTO
10/04/1609
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U.S. PATENT DOCUMENTS

Examiner Initial		Document No.	Name	Date	Class	Subclass	Filing Date (If appropriate)
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	AB	4,237,150	Wiesmann	12/1980	427	74	
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INFORMATION DISCLOSURE STATEMENT PTO-1449	Atty. Docket No. 971003B	Serial No. Not yet assigned
	Applicants: Hideki MATSUMURA et al.	
	Filing Date: January 10, 2002	Group Art Unit: 1763 (Expected)

OTHER DOCUMENTS

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<div style="display: flex; justify-content: space-between; padding: 5px;"> Examiner Date Considered </div>		